

## N-Channel Super Trench II Power MOSFET

### Description

The HMS130N85D uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

- $V_{DS} = 85V, I_D = 130A$   
 $R_{DS(on)} = 3.5m\Omega$  (typical) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

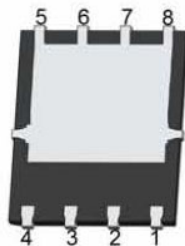
**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

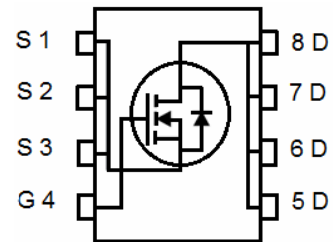
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HMS130N85D	HMS130N85D	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	130	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	93.6	A
Pulsed Drain Current	$I_{DM}$	520	A
Maximum Power Dissipation	$P_D$	150	W
Derating factor		1.2	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	870	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	0.83	$^\circ C/W$
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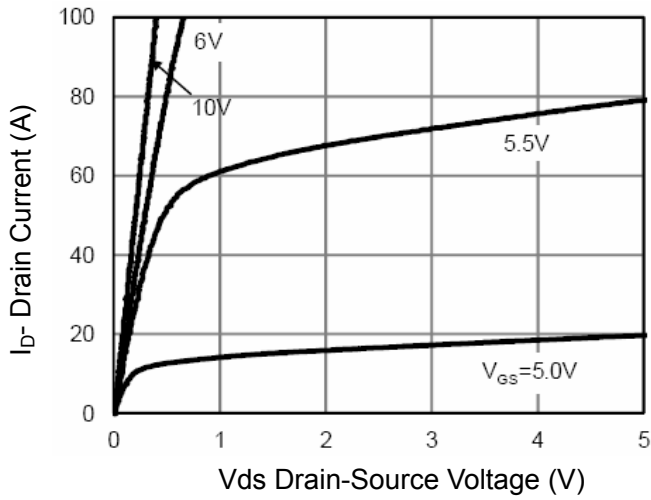
**Electrical Characteristics ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	85		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =65A	-	3.5	4.0	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =65A		60	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V, F=1.0MHz	-	4950	-	PF
Output Capacitance	C <sub>oss</sub>		-	850	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	40	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =40V,I <sub>D</sub> =65A V <sub>GS</sub> =10V,R <sub>G</sub> =3Ω	-	18	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	11	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	38	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	9	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =40V,I <sub>D</sub> =65A, V <sub>GS</sub> =10V	-	88	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	22		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	25		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =65A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	130	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =65A	-	72	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs (Note3)	-	102	-	nC

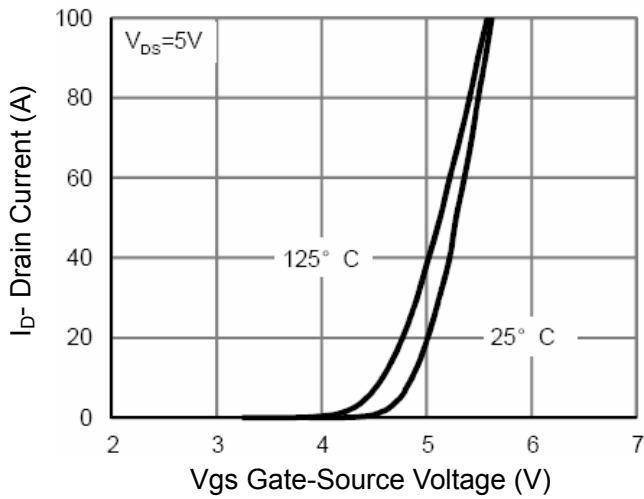
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=40V, V_G=10V, L=0.5mH, R_G=25\Omega$

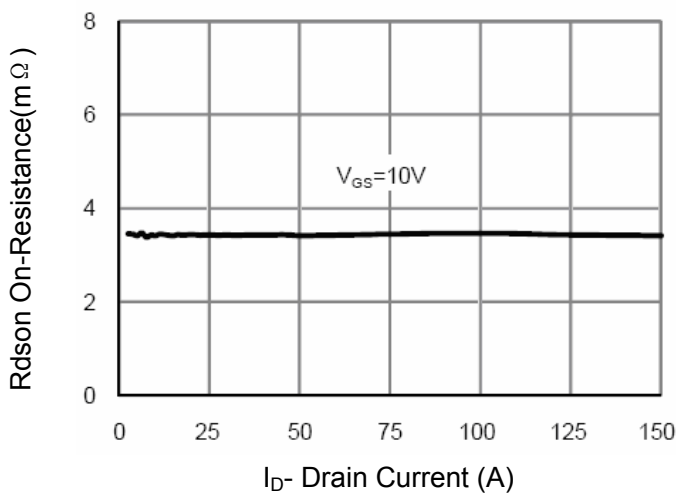
## Typical Electrical and Thermal Characteristics



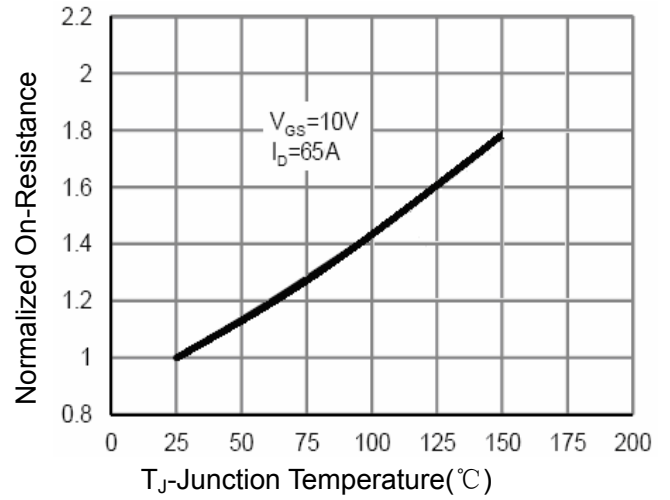
**Figure 1 Output Characteristics**



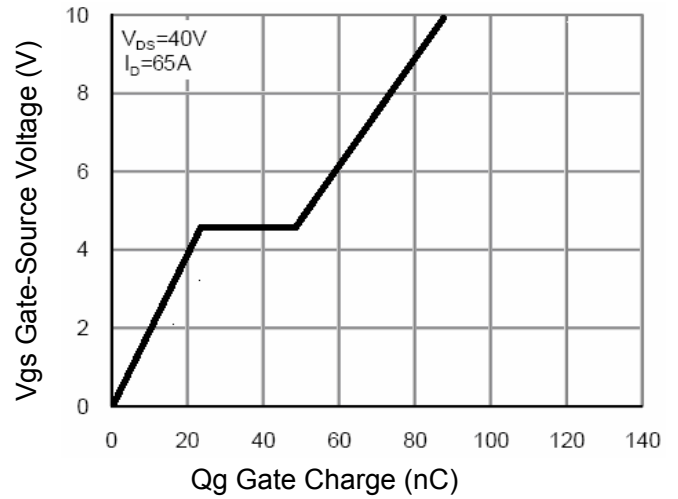
**Figure 2 Transfer Characteristics**



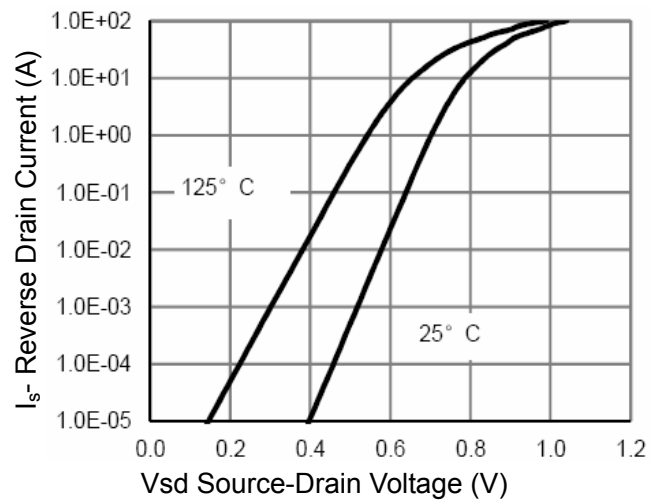
**Figure 3 Rdson- Drain Current**



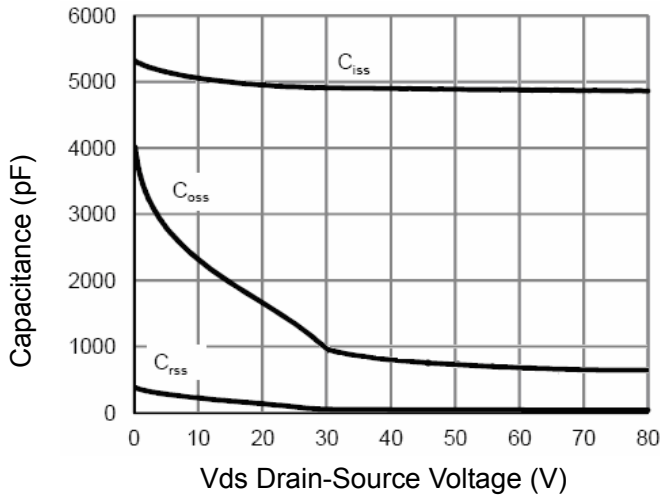
**Figure 4 Rdson-Junction Temperature**



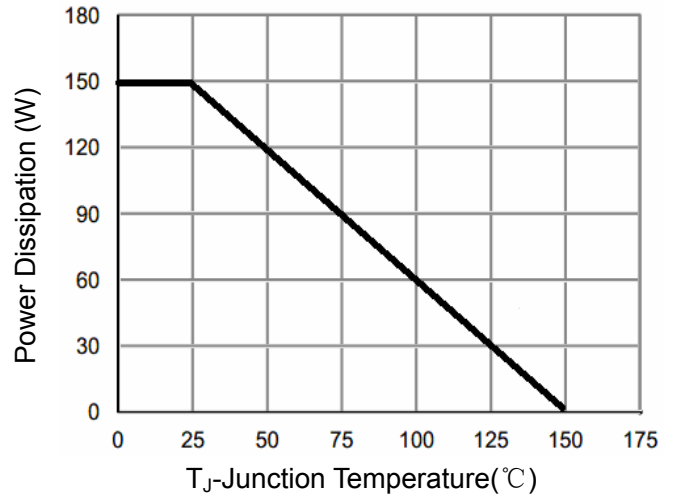
**Figure 5 Gate Charge**



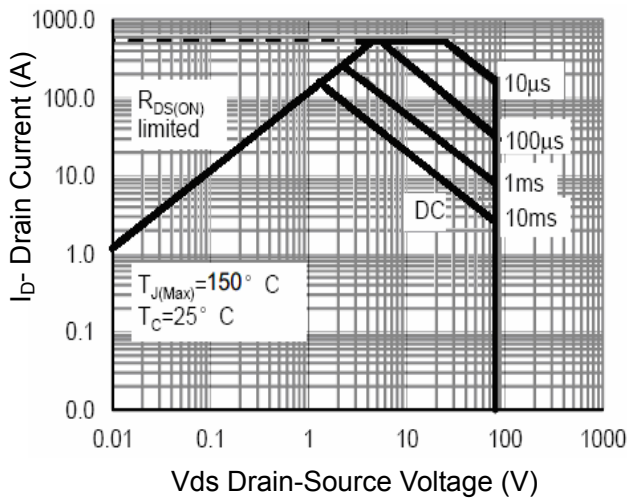
**Figure 6 Source- Drain Diode Forward**



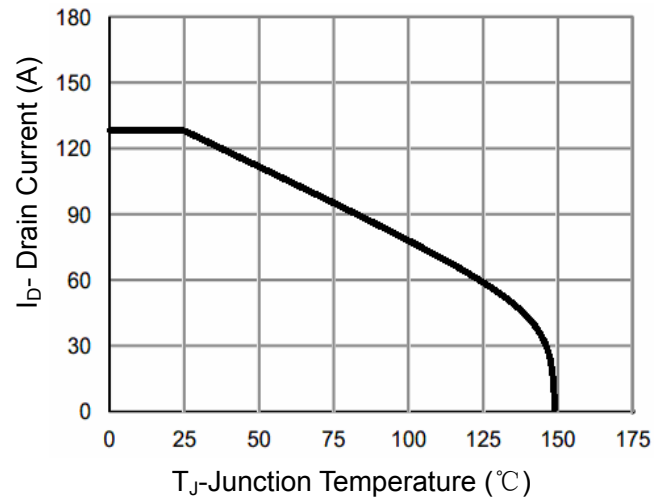
**Figure 7 Capacitance vs Vds**



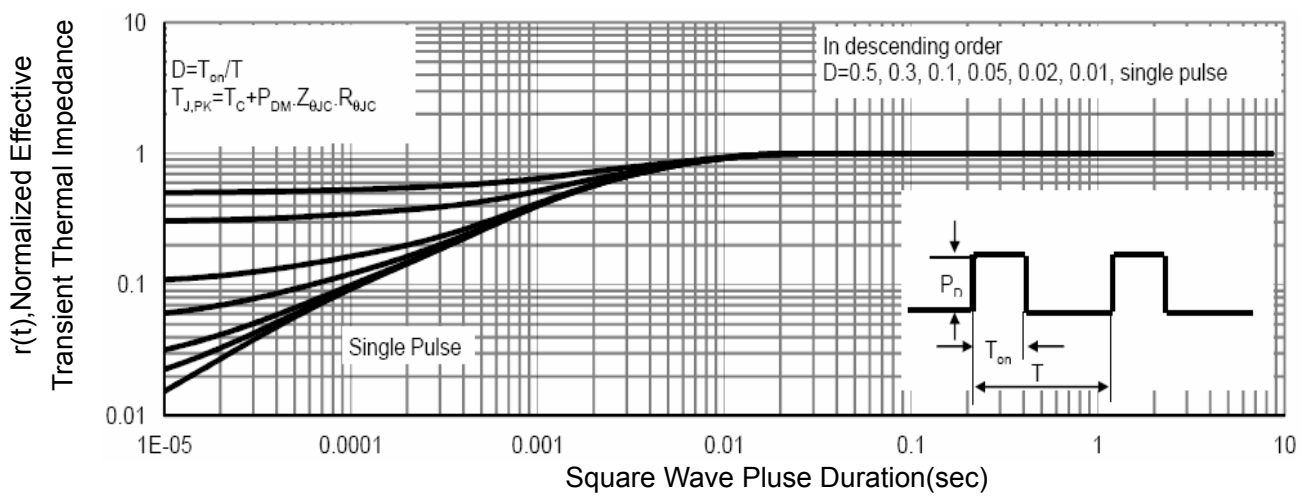
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

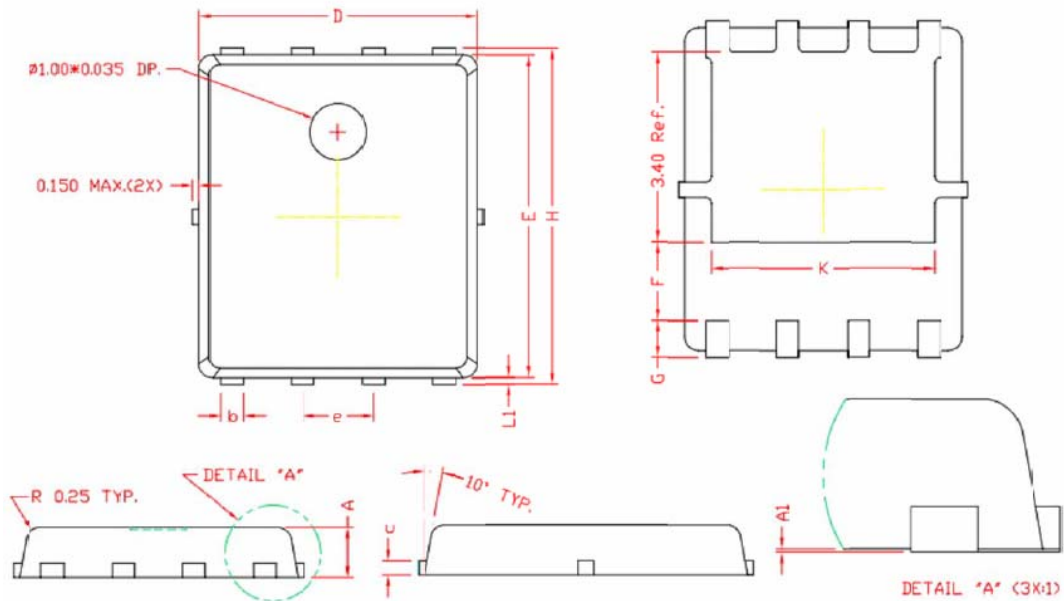


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

DFN5X6-8L Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
b	0.35	0.42	0.49
c	0.254 REF.		
D	4.90	5.00	5.10
F	1.40 REF.		
E	5.70	5.80	5.90
e	1.27 BSC.		
H	5.95	6.08	6.20
L1	0.10	0.14	0.18
G	0.60 REF.		
K	4.00 REF.		